



#### 30V 175°C N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI3333-8

#### **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> Max T <sub>C</sub> = +25°C
30V	$5.5 \text{m}\Omega$ @ $V_{GS} = 10V$	75A
307	$8.5 \text{m}\Omega$ @ $V_{GS} = 4.5 \text{V}$	50A

### **Description and Applications**

This MOSFET is designed to minimize the on-state resistance (R<sub>DS(ON)</sub>) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

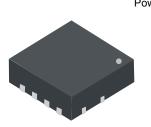
- Engine Management Systems
- Body Control Electronics
- DC-DC Converters

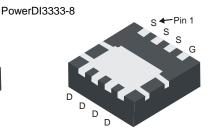
### **Features and Benefits**

- Rated to +175°C Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching (Test in Production) Ensures More Reliable and Robust End Application
- Low R<sub>DS(ON)</sub> Ensures On-State Losses are Minimized
- Excellent Q<sub>qd x</sub> R<sub>DS(ON)</sub> Product (FOM)
- Small Form Factor Thermally Efficient Package Enables Higher Density End Products
- Occupies just 33% of the Board Area Occupied by SO-8 Enabling Smaller End Product
- 100% UIS (Avalanche) Rated
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note4)

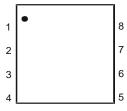
#### **Mechanical Data**

- Case: PowerDI<sup>®</sup>3333-8
- Case Material: Molded Plastic, "Green" Molding Compound.
   UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 3 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
   Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.072 grams (Approximate)

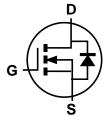




Bottom View







**Equivalent Circuit** 

#### Ordering Information (Note 5)

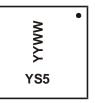
Top View

Part Number	Case	Packaging
DMTH3004LFGQ-7	PowerDI3333-8	2,000/Tape & Reel
DMTH3004LFGQ-13	PowerDI3333-8	3,000/Tape & Reel

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

- 2. See http://www.diodes.com/quality/lead\_free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to Refer to https://www.diodes.com/quality/.
- 5. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

# **Marking Information**



YS5 = Product Type Marking Code YYWW = Date Code Marking YY = Last Two Digits of Year (ex: 18 = 2018) WW = Week Code (01 to 53)



# 

Characteristic		Symbol	Value	Unit
Drain-Source Voltage		$V_{DSS}$	30	V
Gate-Source Voltage		V <sub>GSS</sub>	<u>±</u> 16	V
Continuous Drain Current (Notes 7 & 10) V <sub>GS</sub> = 10V	$T_C = +25$ °C $T_C = +100$ °C	I <sub>D</sub>	75 52	А
Continuous Drain Current (Note 6) $V_{GS} = 10V$ $T_A = +25^{\circ}C$ $T_A = +100^{\circ}C$		I <sub>D</sub>	15 10	А
Maximum Continuous Body Diode Forward Current (Note 6)	Is	3	Α	
Pulsed Drain Current (100µs Pulse, Duty Cycle = 1%)	I <sub>DM</sub>	250	Α	
Pulsed Body Diode Forward Current (100µs Pulse, Duty Cyc	I <sub>SM</sub>	250	A	
Avalanche Current, L=0.3mH	I <sub>AS</sub>	27	A	
Avalanche Energy, L=0.3mH	E <sub>AS</sub>	110	mJ	

# Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 7)	$T_C = +25^{\circ}C$	$P_{D}$	50	W
Thermal Resistance, Junction to Case (Note 7)	$R_{ heta JC}$	3	°C/W	
Total Power Dissipation (Note 6) $T_A = +25^{\circ}C$		$P_{D}$	2.5	W
Thermal Resistance, Junction to Ambient (Note 6)		$R_{ heta JA}$	60	°C/W
Operating and Storage Temperature Range		$T_{J_1}T_{STG}$	-55 to +175	°C

# Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

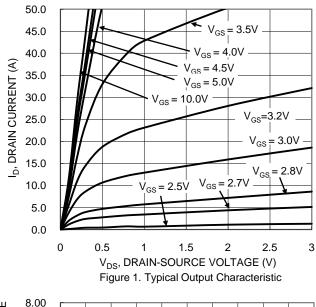
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	30	-	-	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	-	-	1	μΑ	$V_{DS} = 24V$ , $V_{GS} = 0V$	
Gate-Source Leakage	I <sub>GSS</sub>	-	-	±100	nA	$V_{GS} = \pm 16V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage	V <sub>GS(TH)</sub>	1	-	3	<b>V</b>	$V_{DS} = V_{GS}, I_D = 250 \mu A$	
Static Drain-Source On-Resistance		-	4.1	5.5	mΩ	$V_{GS} = 10V, I_D = 20A$	
Static Dialit-Source Off-Resistance	R <sub>DS(ON)</sub>	-	6.2	8.5	11122	$V_{GS} = 4.5V, I_D = 7A$	
Diode Forward Voltage	V <sub>SD</sub>	-	0.7	1	V	$V_{GS} = 0V, I_{S} = 1A$	
DYNAMIC CHARACTERISTICS (Note 9)							
Input Capacitance	C <sub>iss</sub>	-	2370	-		451/1/ 01/	
Output Capacitance	Coss	-	1360	-	pF	$V_{DS} = 15V$ , $V_{GS} = 0V$ , $f = 1MHz$	
Reverse Transfer Capacitance	C <sub>rss</sub>	-	240	-			
Gate Resistance	Rg	-	0.6	-	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$	
Total Gate Charge (V <sub>GS</sub> = 4.5V)	Qg	-	20	-	- 451/ 1 - 004		
Total Gate Charge (V <sub>GS</sub> = 10V)	Qg	-	44	-			
Gate-Source Charge	Q <sub>gs</sub>	-	7	-	nC	$V_{DS} = 15V, I_D = 20A$	
Gate-Drain Charge	$Q_{gd}$	-	8	-			
Turn-On Delay Time	t <sub>D(ON)</sub>	-	6.2	-			
Turn-On Rise Time	t <sub>R</sub>	-	4.3	-	20	$V_{DD} = 15V, V_{GS} = 10V,$ $R_L = 0.75\Omega, R_g = 3\Omega, I_D = 20A$	
Turn-Off Delay Time	t <sub>D(OFF)</sub>	-	21	-	ns		
Turn-Off Fall Time	t <sub>F</sub>	-	8	-			
Body Diode Reverse Recovery Time	t <sub>RR</sub>	-	25	-	ns	1 454 4:/4+ 5004/	
Body Diode Reverse Recovery Charge	Q <sub>RR</sub>	-	37	-	nC	$I_F = 15A$ , di/dt = 500A/ $\mu$ s	

Notes:

- 6.  $R_{\text{0JA}}$  is determined with the device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.  $R_{\text{0JC}}$  is guaranteed by design while R<sub>0JA</sub> is determined by the user's board design.

  7. Thermal resistance from junction to soldering point (on the exposed drain pad).
- 8. Short duration pulse test used to minimize self-heating effect.
- 9. Guaranteed by design. Not subject to product testing.
- 10. Package limited.





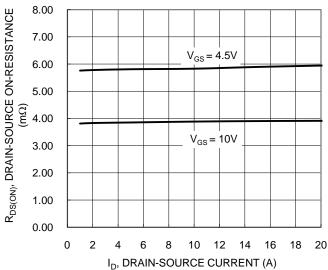


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

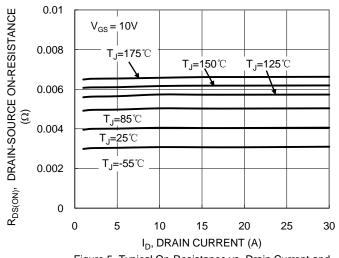


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

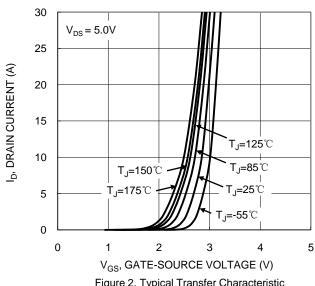


Figure 2. Typical Transfer Characteristic

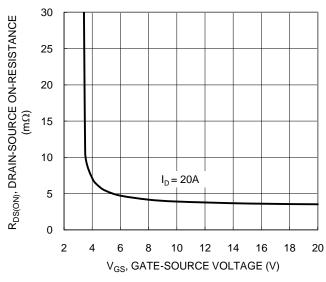


Figure 4. Typical Transfer Characteristic

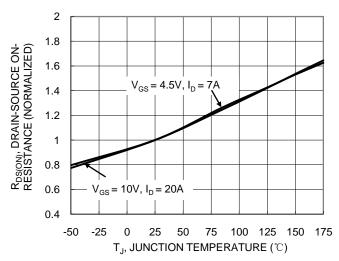


Figure 6. On-Resistance Variation with Temperature



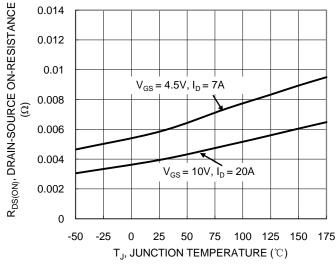


Figure 7. On-Resistance Variation with Temperature

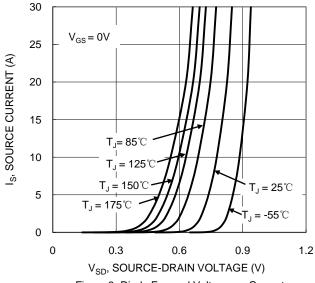


Figure 9. Diode Forward Voltage vs. Current

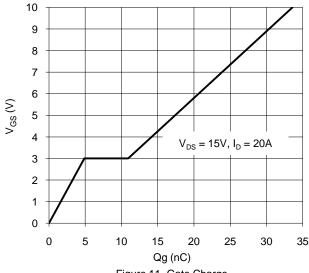


Figure 11. Gate Charge

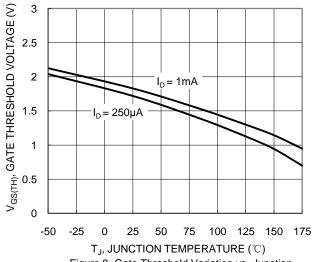
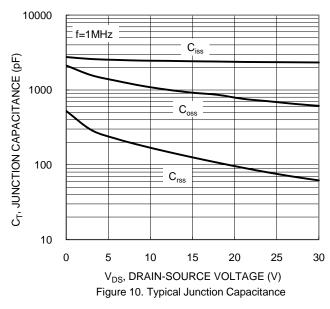


Figure 8. Gate Threshold Variation vs. Junction Temperature



1000 R<sub>DS(ON)</sub> Limited  $P_W = 10 \mu s$ 100 ID, DRAIN CURRENT (A) 10  $P_W = 100 \mu s$ 1  $P_W = 1 \text{ms}$  $T_{J(Max)} = 175^{\circ}C$   $T_C = 25^{\circ}C$ 0.1 P<sub>W</sub> =100ms Single Pulse **DUT** on Infinite Heatsink  $P_W = 1s$ V<sub>GS</sub>= 10V 0.01 0.01 10 100  $V_{DS}$ , DRAIN-SOURCE VOLTAGE (V)

Figure 12. SOA, Safe Operation Area



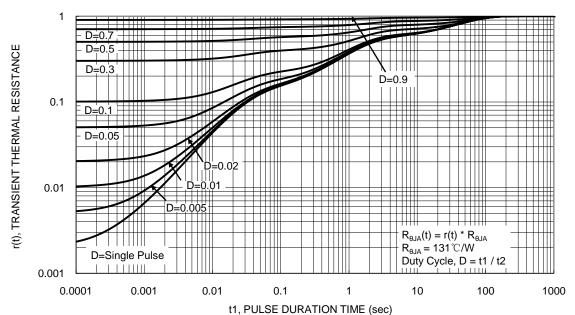


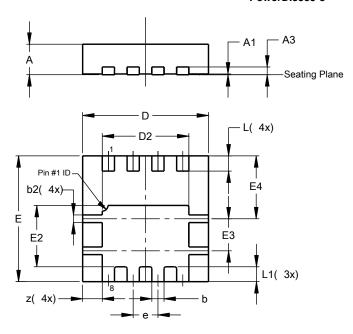
Figure 13. Transient Thermal Resistance



# **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### PowerDI3333-8

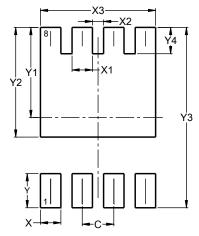


PowerDI3333-8					
Dim	Dim Min		Тур		
Α	0.75	0.85	0.80		
A1	0.00	0.05	0.02		
A3	-	-	0.203		
b	0.27	0.37	0.32		
b2	0.15	0.25	0.20		
D	3.25	3.35	3.30		
D2	2.22	2.32	2.27		
E	3.25	3.35	3.30		
E2	1.56	1.66	1.61		
E3	0.79	0.89	0.84		
E4	1.60	1.70	1.65		
е	_	_	0.65		
L	0.35	0.45	0.40		
L1	_	_	0.39		
Z	_	-	0.515		
All Dimensions in mm					

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### PowerDI3333-8



Dimensions	Value (in mm)
С	0.650
X	0.420
X1	0.420
X2	0.230
Х3	2.370
Υ	0.700
Y1	1.850
Y2	2.250
Y3	3.700
Y4	0.540



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